

MS2422

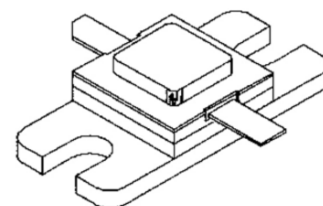
RF & MICROWAVE TRANSISTORS AVIONICS APPLICATIONS

Features

- DESIGNED FOR HIGH POWER PULSED IFF, DME, AND TACAN APPLICATIONS
- 350 W (typ.) IFF 1030 – 1090 MHz
- 300 W (min.) DME 1025 – 1150 MHz
- 290 W (typ.) TACAN 960 – 1215 MHz
- 960 – 1215 MHz
- GOLD METALLIZATION
- $P_{OUT} = 300W$ MINIMUM
- $G_p = 6.3$ dB MINIMUM
- INFINITE VSWR CAPABILITY @ RATED CONDITIONS
- EMITTER BALLASTED
- COMMON BASE

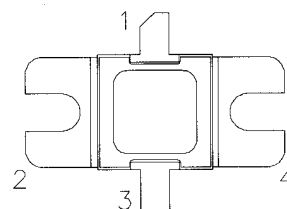
DESCRIPTION:

The MS2422 is a gold metallized silicon, NPN power transistor designed for applications requiring high peak power and low duty cycles such as IFF, DME, and TACAN. The MS2422 is designed with internal input/output matching resulting in improved broadband performance and low thermal resistance.



.400 SQ. 2LFL (M138)
hermetically sealed

PIN CONNECTION



- | | |
|--------------|------------|
| 1. Collector | 3. Emitter |
| 2. Base | 4. Base |

ABSOLUTE MAXIMUM RATINGS (T_{case} = 25°C)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	65	V
V_{CES}	Collector-Emitter Voltage	65	V
V_{EBO}	Emitter-Base Voltage	3.5	V
I_C	Device Current	22	A
P_{DISS}	Power Dissipation	875	W
T_J	Junction Temperature	200	°C
T_{STG}	Storage Temperature	-65 to +150	°C

Thermal Data

$R_{TH(J-C)}$	Junction-case Thermal Resistance	0.20	°C/W
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ELECTRICAL SPECIFICATIONS (T_{case} = 25°C)
STATIC

Symbol	Test Conditions	Value			Unit
		Min.	Typ.	Max.	
BV_{CBO}	I_C = 10 mA I_E = 0 mA	65	---	---	V
BV_{CES}	I_C = 25 mA V_{BE} = 0 V	65	---	---	V
BV_{EBO}	I_E = 5.0 mA I_C = 0 mA	3.5	---	---	V
I_{CES}	V_{CE} = 50 V I_E = 0 mA	---	---	25	mA
h_{FE}	V_{CE} = 5 V I_C = 1A	10	---	---	mA

DYNAMIC

Symbol	Test Conditions	Value			Unit
		Min.	Typ.	Max.	
P_{OUT}	f = 1025 - 1150 MHz P_{IN} = 70W V_{CE} = 50V	300	---	---	W
G_p	f = 1025 - 1150 MHz P_{IN} = 70W V_{CE} = 50V	6.3	---	---	dB
η_C	f = 1025 - 1150 MHz P_{IN} = 70W V_{CE} = 50V	35	---	---	%
Conditions	Pulse Width = 10 μs Duty Cycle = 1%				

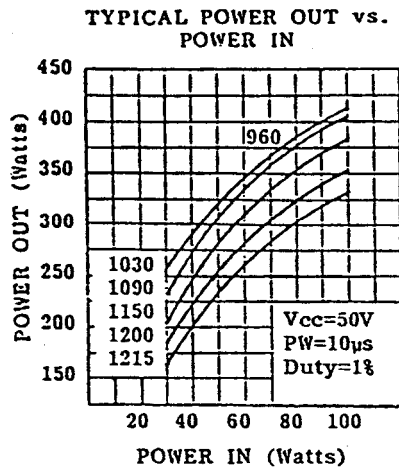
IMPEDANCE DATA

FREQ	Z_{IN}(Ω)	Z_{CL}(Ω)
960 MHz	5.1 + j1.0	2.2 – j3.5
1090 MHz	4.2 + j0.5	2.5 – j3.5
1215 MHz	7.5 + j1.5	2.3 – j1.5

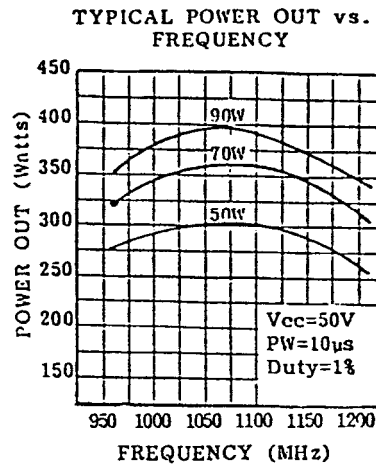
P_{in} = 70W V_{ce} = 50V

TYPICAL PERFORMANCE

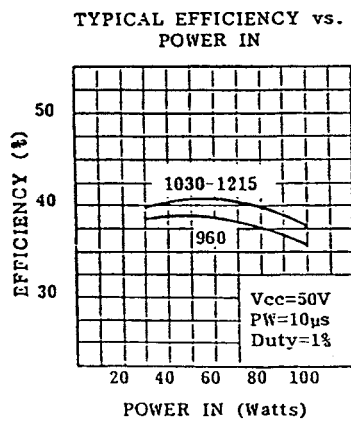
POWER OUTPUT vs POWER INPUT



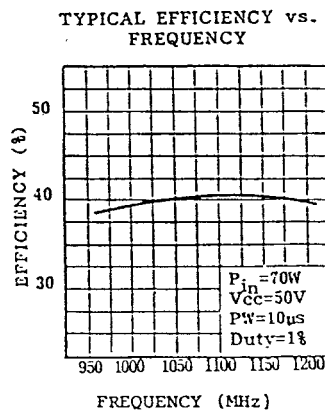
POWER OUTPUT vs FREQUENCY



EFFICIENCY vs POWER INPUT

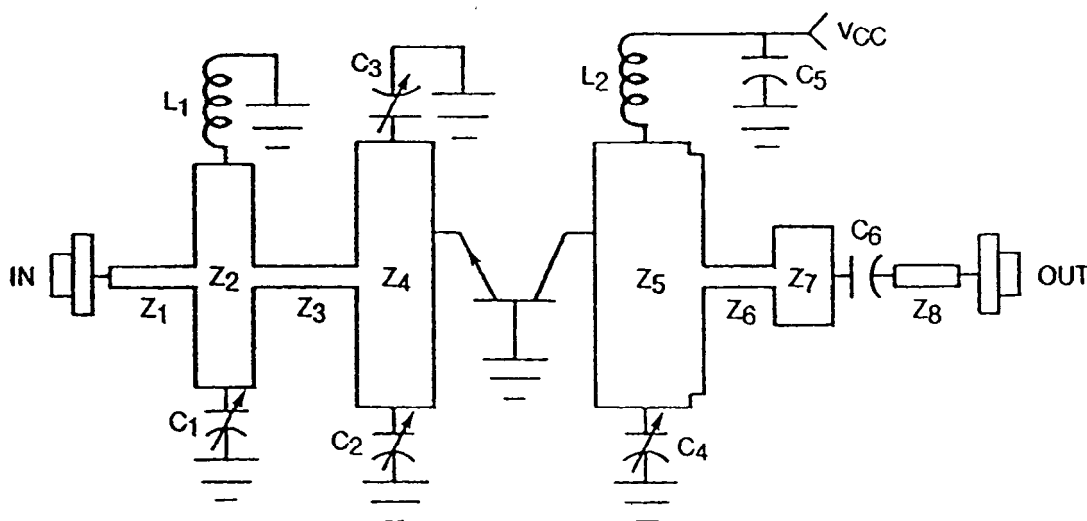


EFFICIENCY vs FREQUENCY



TEST CIRCUIT

Teflon Fiberglass $\epsilon_r = 2.5$ THK .031

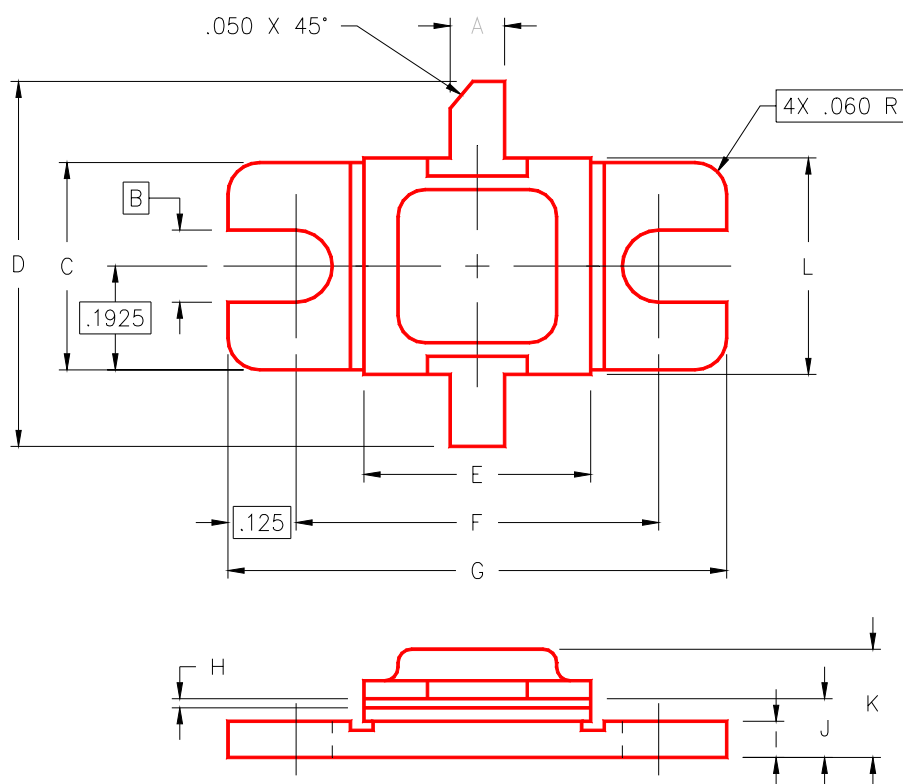


All Dimension are in Inches

C1, C2:	Z1	: .404 x .075
C3, C4 : .6 - 4.5pF JOHANSON Gigatrim	Z2	: .263 x .995
C5 : 1000 μ F, 63V, Electrolytic	Z3	: .483 x .077
C6 : 100pF Chip Capacitor Across .090 Gap	Z4	: .350 x 1.203
L1 : 2 Turns #24 .12 I.D., Spaced Wire Diameter	Z5	: .505 x 1.200 with Two Notches .05 Long By .068 Wide
L2 : 4 Turns #24, .07 I.D., Spaced Wire Diameter	Z6	: .335 x .076
	Z7	: .260 x .442
	Z8	: .310 x .082

PACKAGE MECHANICAL DATA

PACKAGE STYLE M138



	MINIMUM INCHES/MM	MAXIMUM INCHES/MM		MINIMUM INCHES/MM	MAXIMUM INCHES/MM
A	.095/2,41	.105/2,67	I	.055/1,40	.065/1,65
B	.125/3,18		J	.105/2,67	.125/3,18
C	.380/9,65	.390/9,91	K		.230/5,84
D	.790/20,07		L	.392/9,96	.402/10,21
E	.392/9,96	.402/10,21			
F	.645/16,38	.655/16,64			
G	.895/22,73	.905/22,99			
H	.002/0,05	.006/0,15			